

Notice of References Cited

Application/Control No.

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Applicant(s)/Patent Under
Reexamination
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Examiner

RAKESH K. DHINGRA

Art Unit

1792

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,741,396	04-1998	Loewenstein, Lee M.	438/724
	B	US-			
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	L	US-			
	M	US-			

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.